

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. <u>Unknown</u> 9/258643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: <u>Unknown</u> 2822

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*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



#5

Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>mt</u>	5,886,368	03/23/1999	Forbes, L., et al.	257	77	07/29/97
<u>mt</u>	5,898,197	04/27/1999	Fujiwara, H.	257	317	06/03/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
<u>mt</u>	08-255878-TR	10/01/1996	Japan	H01L	27/10	X

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
<u>mt</u>	Sze, S.M., In: <u>Physics of Semiconductor Devices</u> , Wiley-Interscience, New York, p. 496-497, (1969)

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Examiner <u>Michael Trish</u>	Date Considered <u>6/25/00</u>
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Sheet 1 of 1

Form 1449*

Atty. Docket No.: 303.324US2

Serial No. 09/256,643

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
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Applicant: Leonard Forbes et al.

Filing Date: February 23, 1999

Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
MT	4,849,797	07/18/1989	Ukai, Y., et al.	357	237	01/20/88

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS

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Sheet 1 of 1

Form 1449*	Atty. Docket No.: 303.324US2	Serial No. 09/256,643
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: February 23, 1999	Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
MT	5,049,950	09/17/1991	Fujii, Y., et al.	357	2	08/09/90

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

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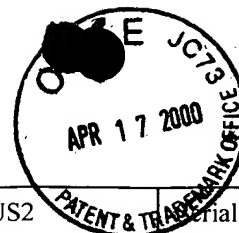
**Examiner Initial	
MT	Sakata, I., et al., "Amorphous silicon/amorphous silicon carbide heterojunctions applied to memory device structures", <u>Electronics Letters</u> , 30(9), pp. 688-689, (April 1994)

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Form 1449* INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No.: 303.324US2		Serial No. 09/256,643
	Applicant: Leonard Forbes et al.		
	Filing Date: February 23, 1999		Group: 2822

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
						If Appropriate
<u>mt</u>	5,235,195	08/10/1993	Tran, N.T., et al.	257	59	10/19/92
<u>I</u>	5,415,126	05/16/1995	Loboda, M.J., et al.	117	88	08/16/93
<u>I</u>	5,455,432	10/03/1995	Hartsell, M.L., et al.	257	77	10/11/94
<u>I</u>	5,562,769	10/08/1996	Dreifus, D.L., et al.	117	86	02/22/95
<u>ma</u>	5,877,041	03/02/1999	Fuller, R.T.	438	105	06/30/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<u>ma</u>	07-226507	08/22/1995	Japan	H01L	29/78		<input checked="" type="checkbox"/>

OTHER DOCUMENTS

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